

PU3219, PU4219, PU4519

Silicon NPN Epitaxial Planar Darlington Type

Power Amplifier, Switching

Complementary Pair with PU3119, PU4119, PU4419

Features

- Low DC current gain (h_{FE})
- High speed switching
- PU3219: 3 NPN elements
- PU4219: 4 NPN elements
- PU4519: 2 NPN elements \times 2 (4 elements in total)

Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

Item	Symbol	Value	Unit
Collector-base voltage	V_{CBO}	-60	V
Collector-emitter voltage	V_{CEO}	-60	V
Emitter-base voltage	V_{EBO}	-5	V
Peak collector current	I_{CP}	-4	A
Collector current	I_C	-2	A
Power dissipation	P_D	15	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ~ +150	$^\circ\text{C}$

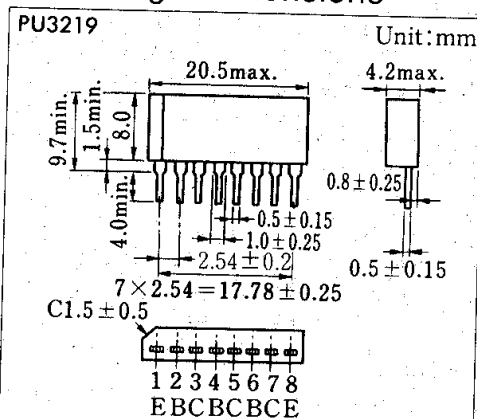
Electrical Characteristics ($T_c=25^\circ\text{C}$)

Item	Symbol	Condition				Unit
			min.	typ.	max.	
Collector cutoff current	I_{CBO}	$V_{CB} = -60\text{V}, I_E = 0$			-1	mA
	I_{CEO}	$V_{CE} = -30\text{V}, I_B = 0$			-2	mA
Emitter cutoff current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$			-2	mA
Collector-emitter voltage	V_{CEO}	$I_C = -30\text{mA}, I_B = 0$	-60			V
DC current gain	h_{FE1}	$V_{CE} = -4\text{V}, I_C = -1\text{A}$	1000			
	h_{FE2}^*	$V_{CE} = -4\text{V}, I_C = -2\text{A}$	1000		10000	
Base-emitter voltage	V_{BE}	$V_{CE} = -4\text{V}, I_C = -2\text{A}$			-2.8	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2\text{A}, I_B = -8\text{mA}$			-2.5	V
Transition frequency	f_T	$V_{CE} = -10\text{V}, I_C = -0.5\text{A}, f = 1\text{MHz}$		20		MHz
Turn-on time	t_{on}	$I_C = -2\text{A}, I_{B1} = -8\text{mA}, I_{B2} = 8\text{mA}$		0.4		μs
Storage time	t_{stg}			1.5		μs
Fall time	t_f			0.5		μs

h_{FE2} Classifications

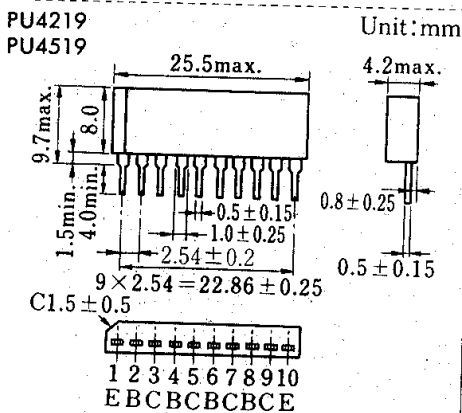
Class	Free	Q	P
h_{FE2}	1000 ~ 10000	1000 ~ 5000	5000 ~ 10000

Package Dimensions



Unit: mm
E: Emitter
B: Base
C: Collector

8-Lead Plastic SIL Package



Unit: mm
E: Emitter
B: Base
C: Collector

10-Lead Plastic SIL Package